



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: Hin-Yiu Chung ET AL.

Appln. No.: Not yet assigned

Filed: Herewith

For:

METHOD FOR OXIDIZING A

LAYER, AND ASSOCIATED HOLDING DEVICES FOR A

SUBSTRATE

Attorney Docket No: 10808/200

Examiner: Not yet assigned

Art Unit: N/A

INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following reference(s):

| No. Date of Publication | | Patentee/Applicant/Assignee | | | |
|--|---------------------|-----------------------------|--|--|--|
| US 2002/0026900 A1 | March 7, 2002 | Huang et al. | | | |
| 6,342,691 B1 | January 29, 2002 | Johnsgard et al. | | | |
| 5,872,889 | February 16, 1999 | Kaltenbrunner et al. | | | |
| 5,635,409 | June 3, 1997 | Meslehi | | | |
| 5,581,571 | December 3, 1996 | Holonyak, Jr. et al. | | | |
| 5,385,866 | January 31, 1995 | Bartush | | | |
| 5,313,044 | May 17, 1994 | Massoud et al. | | | |
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| | FOREIGN PATENT DOCL | IMENTS | | | |
| DOCUMENT | | | | | |
| NUMBER | DATE | COUNTRY | | | |
| GB 2 355 850 A | May 2, 2001 | United Kingdom | | | |
| WO 99/03141 | January 21, 1999 | WO | | | |
| GB 2 295 271 A | May 22, 1996 | United Kingdom | | | |
| DE 689 19 408 T2 | September 29, 1989 | Germany | | | |
| DE 37 50 382 T2 | March 4, 1987 | Germany | | | |
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| OTHER ART – NON PATENT LITERATURE DOCUMENTS | | | | | |
| Spezialgraphite von SGL Carbon, Produkte für die Halbleitertechnik, SGL Carbon Group, | | | | | |
| pgs. 2-17, | | | | | |
| H.Q. Jia, H. Chen, W.C. Wang, W.X. Wang, W. Li, Q. Huang and Jiunming Zhou, <i>The Study</i> | | | | | |
| of Thermal Stability During Wet Oxidation of AIAS, Institute of Physics, Chinese Academy of | | | | | |
| Sciences, pgs. 484-488, Journal of Crystal Growth, Vol. 223, Issue 4, March 2001. | | | | | |
| William G. Breiland, Michael E. Coltrin, J. Randall Creighton, Hong Q. Hou, Harry K. Moffat | | | | | |
| and Jeffrey Y. Tsao, Organometalic Vapor Phase Epitaxy, Center for Compound | | | | | |
| Semiconductor Science and Technology, Sandia National Laboratories, Materials Science | | | | | |

Copy of International Search Report from International Application Number PCT/DE/02523.

Copy of Examination Report from International Application Number PCT/DE/02523.

and Engineering: R. Reports, Vol. 24, Issue 6, pgs. 241-274, February 1999.

ttorney Docket No. 10808/200

Applicants are enclosing Form PTO-1449 (one sheet), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary, 37 C.F.R §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

Anthony P. Curtis, Ph.D.

(Reg. No. 46/193)



| FORM PTO-1449 | SERIAL NO. | CASE NO. |
|--------------------------------------|------------------------------------|------------------|
| | Not yet assigned | 10808/200 |
| LIST OF PATENTS AND PUBLICATIONS FOR | FILING DATE | GROUP ART UNIT |
| APPLICANT'S INFORMATION DISCLOSURE | Herewith | Not yet assigned |
| STATEMENT | | |
| (use several sheets if necessary) | APPLICANT(S): Hin-Yiu Chung et al. | |

REFERENCE DESIGNATION

| U.S. | PATENT DOCUMEN | ITS |
|------|----------------|-----|
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| EXAMINER INITIAL | | DOCUMENT NUMBER Number-Kind Code (if known) | DATE | NAME | CLASS/ SUBCLASS | FILING DATE |
|---------------------|----|---|-------------------|----------------------|--------------------|----------------|
| | A1 | US 2002/0026900 A1 | March 7, 2002 | Huang et al. | | |
| | A2 | 6,342,691 B1 | January 29, 2002 | Johnsgard et al. | | |
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FOREIGN PATENT DOCUMENTS

| EXAMINER INITIAL | | DOCUMENT NUMBER Number-Kind Code (if known) | DATE | COUNTRY | CLASS/ SUBCLASS | TRANSLATION YES OR NO |
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| | A8 | GB 2 355 850 A | May 2, 2001 | United Kingdom | | |
| | A9 | WO 99/03141 | January 21, 1999 | WO | | <u> </u> |
| | A10 | GB 2 295 271 A | May 22, 1996 | United Kingdom | | |
| | A11 | DE 689 19 408 T2 | September 29, 1989 | Germany | | |
| | A12 | DE 37 50 382 T2 | March 4, 1987 | Germany | | |

| EXAMINER INITIAL | (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where pu | | |
|---------------------|--|---|--|
| | A13 | Spezialgraphite von SGL Carbon, Produkte für die Halbleitertechnik, SGL Carbon Group, pgs. 2-17, | |
| | A14 | H.Q. Jia, H. Chen, W.C. Wang, W.X. Wang, W. Li, Q. Huang and Jiunming Zhou, <i>The Study of Thermal Stability During Wet Oxidation of AIAS</i> , Institute of Physics, Chinese Academy of Sciences, pgs. 484-488, Journal of Crystal Growth, Vol. 223, Issue 4, March 2001. | |
| | A15 | William G. Breiland, Michael E. Coltrin, J. Randall Creighton, Hong Q. Hou, Harry K. Moffat and Jeffrey Y. Tsao, <i>Organometalic Vapor Phase Epitaxy</i> , Center for Compound Semiconductor Science and Technology, Sandia National Laboratories, Materials Science and Engineering: R. Reports, Vol. 24, Issue 6, pgs. 241-274, February 1999. | |
| | A16 | Copy of International Search Report from International Application Number PCT/DE/02523. | |
| | A17 | Copy of Examination Report from International Application Number PCT/DE/02523. | |

| EXAMINER | DATE CONSIDERED |
|----------|-----------------|
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.